



N-Channel NexFET™ Power MOSFET

Check for Samples: CSD16414Q5

FEATURES

- Ultra Low Qg and Qgd
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5mm × 6mm Plastic Package

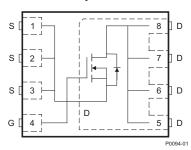
APPLICATIONS

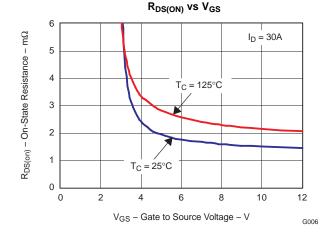
- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Synchronous FET Applications

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.

Top View





PRODUCT SUMMARY

V _{DS}	Drain to Source Voltage 25			
Q_g	Gate Charge Total (4.5V) 16.6			
Q _{gd}	Gate Charge Gate to Drain	4.4		nC
Б	Design to Course On Basistana	V _{GS} = 4.5V	2.1	mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10V	1.5	mΩ
V _{GS(th)}	Threshold Voltage	1.6	V	

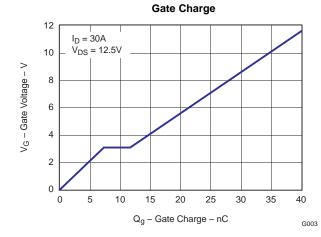
ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD16414Q5	SON 5 x 6 Plastic Package	13-inch reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 2$	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+16 / -12	٧
	Continuous Drain Current, T _C = 25°C	100	Α
I _D	Continuous Drain Current ⁽¹⁾	34	Α
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	213	Α
P_D	Power Dissipation ⁽¹⁾	3.2	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse I_D = 100A, L = 0.1mH, R_G = 25 Ω	500	mJ

- (1) $R_{\theta JA} = 39^{\circ}C/W$ on $1in^2$ Cu (2 oz.) on 0.060" thick FR4 PCB.
- (2) Pulse width ≤300μs, duty cycle ≤2%"





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



ELECTRICAL CHARACTERISTICS

 $(T_{\Delta} = 25^{\circ}C \text{ unless otherwise stated})$

$(1_A = 25)$	°C unless otherwise stated)			1	
	PARAMETER	TEST CONDITIONS	MIN TY	P MAX	UNIT
Static C	haracteristics				
BV_{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25		V
I_{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 20V$		1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +16/-12V$		100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.3 1.	5 2	V
D	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 30A$	2.	1 2.6	$m\Omega$
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 10V, I_D = 30A$	1.	5 1.9	$m\Omega$
g _{fs}	Transconductance	$V_{DS} = 15V, I_D = 30A$	13	3	S
Dynamic	C Characteristics				
C _{ISS}	Input Capacitance		281	3650	pF
C _{OSS}	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V, f = 1MHz$	204	2650	pF
C _{RSS}	Reverse Transfer Capacitance		14	180	pF
R_g	Series Gate Resistance		1.	4 2.8	Ω
Qg	Gate Charge Total (4.5V)		16.	3 21	nC
Q _{gd}	Gate Charge Gate to Drain	V 40.5V ID 200	4.	4	nC
Q _{gs}	Gate Charge Gate to Source	V _{DS} = 12.5V, ID = 30A	7.3	3	nC
Qg(th)	Gate Charge at Vth		4.	5	nC
Q _{OSS}	Output Charge	V _{DS} = 13.5V, VGS = 0V	4)	nC
t _{d(on)}	Turn On Delay Time		1:	5	ns
t _r	Rise Time	V _{DS} = 12.5V, V _{GS} = 4.5V, I _D = 30A	2	4	ns
t _{d(off)}	Turn Off Delay Time	$R_G = 2\Omega$	18.	4	ns
t _f	Fall Time		11.	1	ns
Diode C	haracteristics				
V _{SD}	Diode Forward Voltage	I _S = 30A, V _{GS} = 0V	0.8	1 1	V
Q _{rr}	Reverse Recovery Charge	$V_{dd} = 13.5V$, $I_F = 30A$, $di/dt = 300A/\mu s$	4	4	nC
t _{rr}	Reverse Recovery Time	$V_{dd} = 13.5V$, $I_F = 30A$, $di/dt = 300A/\mu s$	3	5	ns

THERMAL CHARACTERISTICS

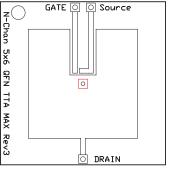
 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	MIN	TYP	MAX	UNIT
R ₀ JC	Thermal Resistance Junction to Case (1)			1.1	°C/W
R _{θJA}	Thermal Resistance Junction to Ambient ⁽¹⁾ (2)			50	°C/W

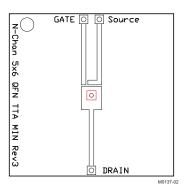
⁽¹⁾ R $_{\theta JC}$ is determined with the device mounted on a 1 inch square 2 oz. Cu pad on a 1.5 x 1.5 in 0.060 inch thick FR4 board. R $_{\theta JC}$ is specified by design while R $_{\theta JA}$ is determined by the user's board design.

⁽²⁾ Device mounted on FR4 Material with 1 inch² of 2 oz. Cu.





Max $R_{\theta JA} = 50$ °C/W when mounted on 1inch² of 2 oz. Cu.



Max $R_{\theta JA} = 122^{\circ}C/W$ when mounted on minimum pad area of 2 oz. Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

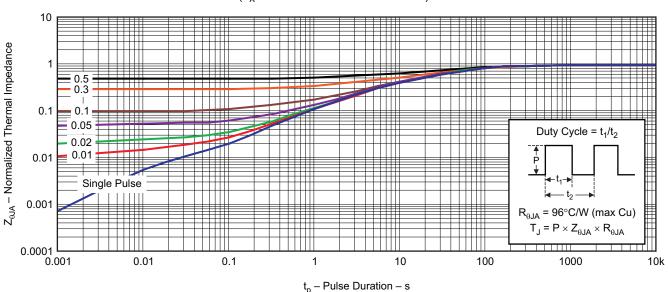


Figure 1. Transient Thermal Impedance



TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

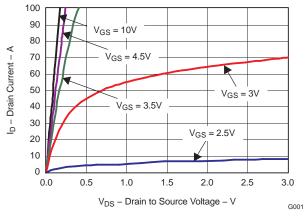


Figure 2. Saturation Characteristics

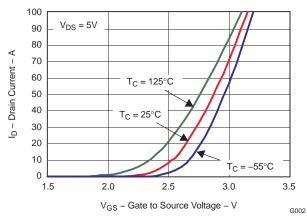


Figure 3. Transfer Characteristics

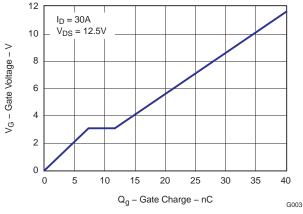


Figure 4. Gate Charge

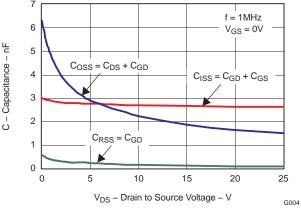


Figure 5. Capacitance

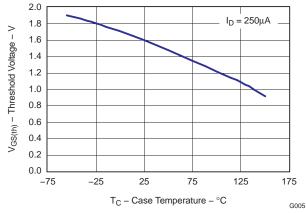


Figure 6. Threshold Voltage vs. Temperature

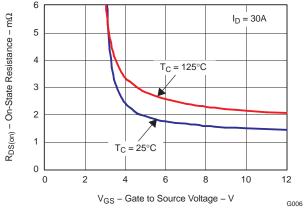


Figure 7. On Resistance vs. Gate Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

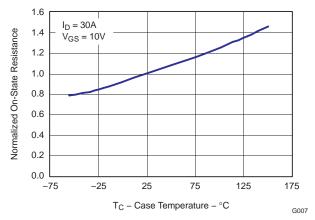


Figure 8. On Resistance vs. Temperature

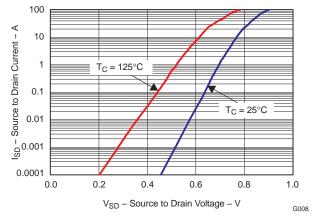


Figure 9. Typical Diode Forward Voltage

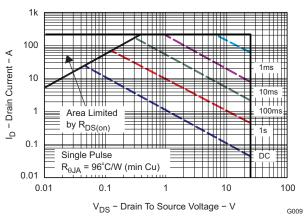


Figure 10. Maximum Safe Operating Area

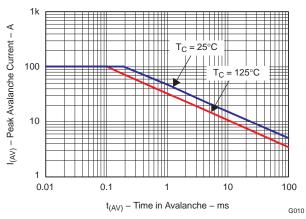


Figure 11. Single Pulse Unclamped Inductive Switching

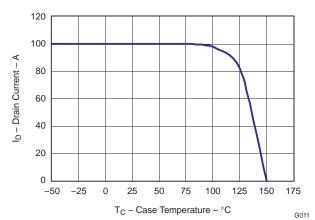
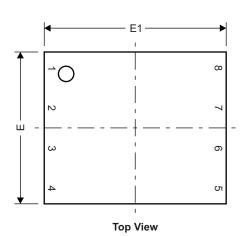


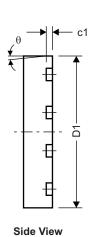
Figure 12. Maximum Drain Current vs. Temperature

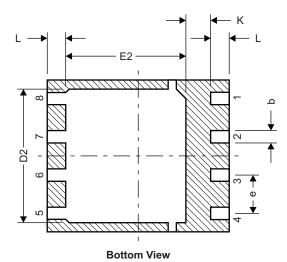


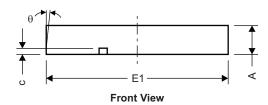
MECHANICAL DATA

Q5 Package Dimensions





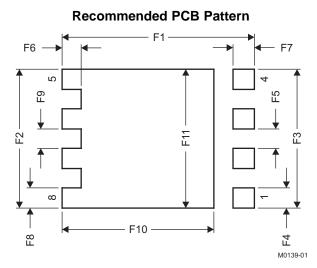




M0140-01

DIM	MILLIM	ETERS	INCHES		
DIW	MIN	MAX	MIN	MAX	
Α	0.950	1.050	0.037	0.039	
b	0.360	0.460	0.014	0.018	
С	0.150	0.250	0.006	0.010	
c1	0.150	0.250	0.006	0.010	
D1	4.900	5.100	0.193	0.201	
D2	4.320	4.520	0.170	0.178	
E	4.900	5.100	0.193	0.201	
E1	5.900	6.100	0.232	0.240	
E2	3.920	4.12	0.154	0.162	
е	1.27	TYP	0.0	050	
K	0.760		0.030		
L	0.510	0.710	0.020	0.028	
θ	0.00				

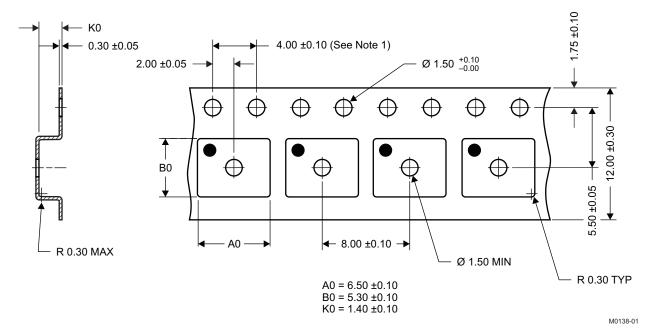




DIM	MILLIM	ETERS	INC	HES
DIN	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.460	4.560	0.176	0.180
F3	4.460	4.560	0.176	0.180
F4	0.650	0.700	0.026	0.028
F5	0.620	0.670	0.024	0.026
F6	0.630	0.680	0.025	0.027
F7	0.700	0.800	0.028	0.031
F8	0.650	0.700	0.026	0.028
F9	0.620	0.670	0.024	0.026
F10	4.900	5.000	0.193	0.197
F11	4.460	4.560	0.176	0.180

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q5 Tape and Reel Information



Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. Thickness: 0.30 ±0.05mm
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible



REVISION HISTORY

Cł	changes from Original (August 2009) to Revision A	Page
•	Deleted the Package Marking Information section	

PACKAGE MATERIALS INFORMATION

www.ti.com 21-Jan-2011

TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16414Q5	SON	DQH	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1

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*All dimensions are nominal

I	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
I	CSD16414Q5	SON	DQH	8	2500	335.0	335.0	32.0

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